ALPHA & OMEGA
SEMICONDUCTOR

AOK065V120X2

1200V αSiC Silicon Carbide Power MOSFET

Features

- Proprietary αSiC MOSFET technology
- Low loss, fast switching speeds with low R_G
- Optimized drive voltage (V_{GS} =15V) for broad driver compatibility
- Robust body diode and low Qrr

Product Summary

V_{DS} @ $T_{J,\,max}$	1200V
I_{DM}	85A
$R_{DS(ON),\,typ}$	65mΩ
Q_{rr}	164nC
E_{OSS} @ 800V	36μJ
100% UIS Tested	

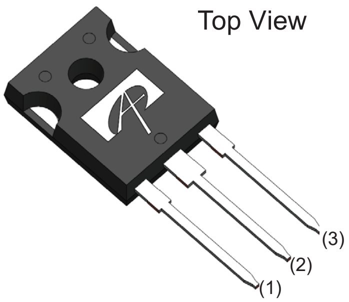
RoHS Compliant

Applications

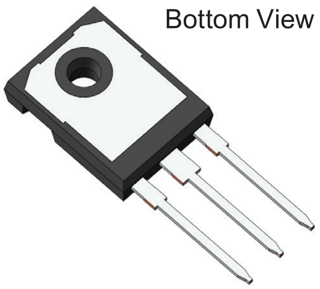
- Renewable
- EV Charger
- Solar Inverters
- Industrial
- UPS
- SMPS
- Motor Drives

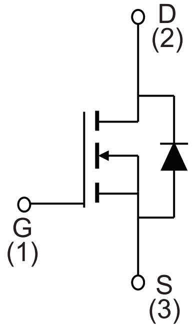
Pin Configuration

Top View



Bottom View





Ordering Part Number	Package Type	Form	Shipping Quantity
AOK065V120X2	TO-247-3L	Tube	30/Tube

Absolute Maximum Ratings

(T_A = 25°C, unless otherwise noted)

Symbol	Parameter		AOK065V120X2	Units
V_{DS}	Drain-Source Voltage		1200	V
$V_{GS,\,MAX}$	Gate-Source Voltage	Maximum	-8/+18	V
$V_{GS,OP,TRANS}$		Max Transient$^{(A)}$	-8/+20	
$V_{GS,OP}$		Recommended Operating $^{(B)}$	-5/+15	
I_D	Continuous Drain Current	T_C = 25°C	40.3	A
		T_C = 100°C	29.6	
I_{DM}	Pulsed Drain Current$^{(C)}$		85	
E_{AS}	Single Pulsed Avalanche Energy$^{(D)}$		250	mJ
P_D	Power Dissipation$^{(C)}$		187.5	W
T_J, T_{STG}	Junction and Storage Temperature Range		-55 to 175	°C
T_L	Maximum lead temperature for soldering purpose, 1/8” from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	AOK065V120X2	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient $^{(E,F)}$	40	°C/W
$R_{\theta JC}$	Maximum Junction-to-Case $^{(G)}$	0.8	°C/W

Electrical Characteristics

(T_A = 25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V, T_J=25°C	1200			V
		I_D=250µA, V_{GS}=0V, T_J=150°C		1200		V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=1200V, V_{GS}=0V, T_J=150°C			1	µA
I_{GSS}	Gate-Source Leakage Current	V_{DS}=0V, V_{GS}=+15/-5V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=5V, I_D=250µA	1.8	2.8	3.5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=15V, I_D=20A, T_J = 25°C		65	85	mΩ
		T_J= 150°C		90		mΩ
g_{fs}	Forward Transconductance	V_{DS}=20V, I_D=20V		12		S
V_{SD}	Diode Forward Voltage	I_S=10A,V_{GS}=-5V		4.1	5	V
DYNAMIC						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=800V, f=1MHz		1716		pF
C_{oss}	Output Capacitance			71		pF
C_{rss}	Reverse Transfer Capacitance			5		pF
E_{oss}	Coss Stored Energy			30		µJ
R_G	Gate Resistance	f=1MHz		2.5		Ω
SWITCHING						
Q_g	Total Gate Charge	V_{GS}=-5/+15V, V_{DS}=800V, I_D=20A		62.3		nC
Q_{gs}	Gate Source Charge			23.1		nC
Q_{gd}	Gate Drain Charge			23.7		nC
$t_{d(on)}$	Turn-On DelayTime	V_{GS}=0V/+15V, V_{DS}=800V, I_D=20A, R_G=5Ω La = 120µH FWD: AOK065V120X2		14.6		ns
t_r	Turn-On Rise Time			36.2		ns
$t_{d(off)}$	Turn-Off DelayTime			20.8		ns
t_f	Turn-Off Fall Time			10.2		ns
E_{on}	Turn-On Energy			325		µJ
E_{off}	Turn-Off Energy			23		µJ
E_{tot}	Total Switching Energy			348		µJ
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A,dI/dt=1560A/us, V_{DS}=800V		27		ns
I_{rm}	Peak Reverse Recovery Current			10		A
Q_{rr}	Body Diode Reverse Recovery Charge			155		nC

Notes:

A. < 1% duty cycle, f >1Hz

B. Device can be operated at V_{GS}=0/15V. Actual operating VGS will depend on application specifics such as parasitic inductance and dV/dt but should not exceed maximum ratings.

C. The power dissipation P_D is based on $T_{J(MAX)}$=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

D. L=5mH, I_{AS}=4.3A, R_G=25Ω, Starting T_J=25°C.

E. The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A =25°C.

F. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

G. The value of $R_{\theta JC}$ is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=175°C.

H. The static characteristics in Figures 1 to 8 are obtained using <300ms pulses, duty cycle 0.5% max.

I. These curves are based on $R_{\theta JC}$ which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$ =175°C.The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

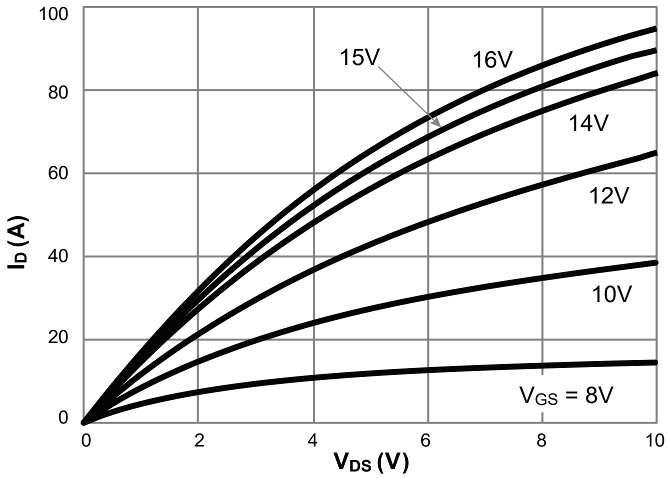


Figure 1. On-Region Characteristics T_J = 25°C

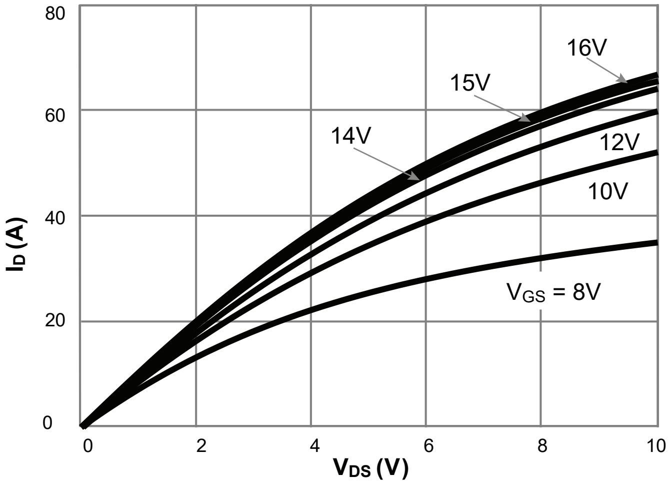


Figure 2. On-Region Characteristics T_J = 175°C

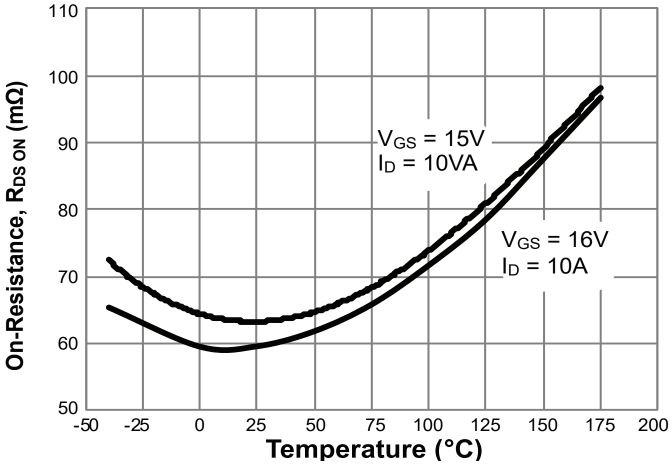


Figure 3. On-Resistance vs. Junction Temperature

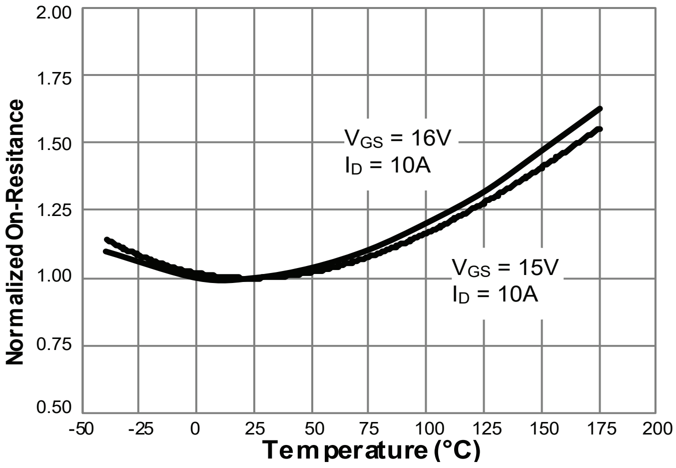


Figure 4. Normalized On-Resistance vs. Junction Temperature

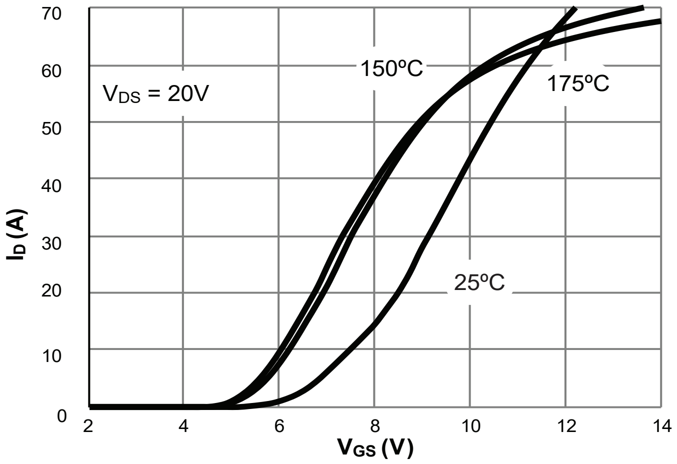


Figure 5. Transfer Characteristics

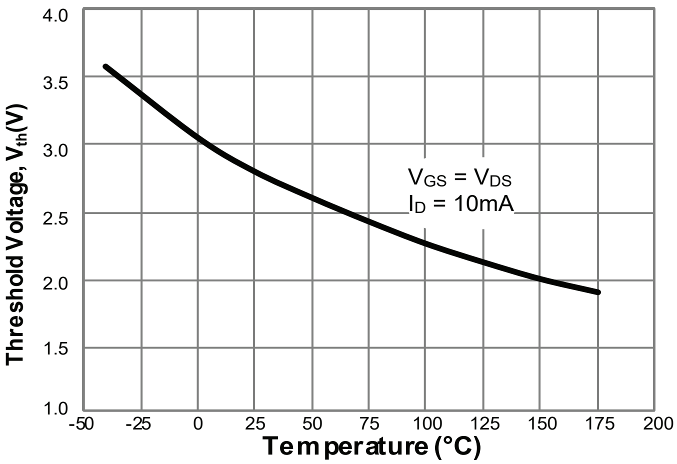


Figure 6. Threshold Voltage vs. Junction Temperature

Typical Electrical and Thermal Characteristics

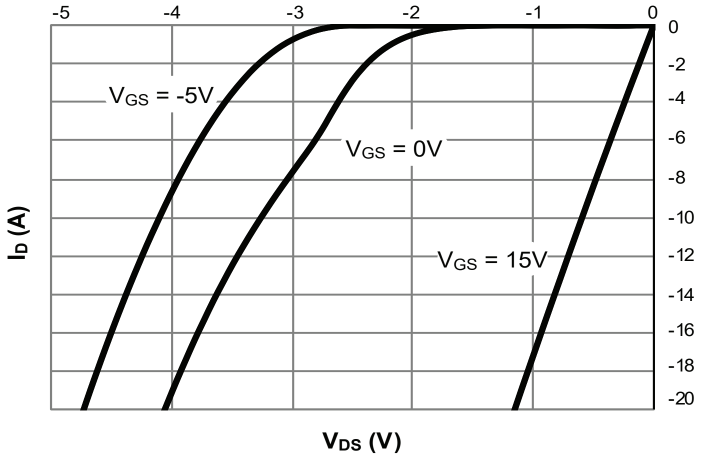


Figure 7. Body-Diode Characteristics at 25°C

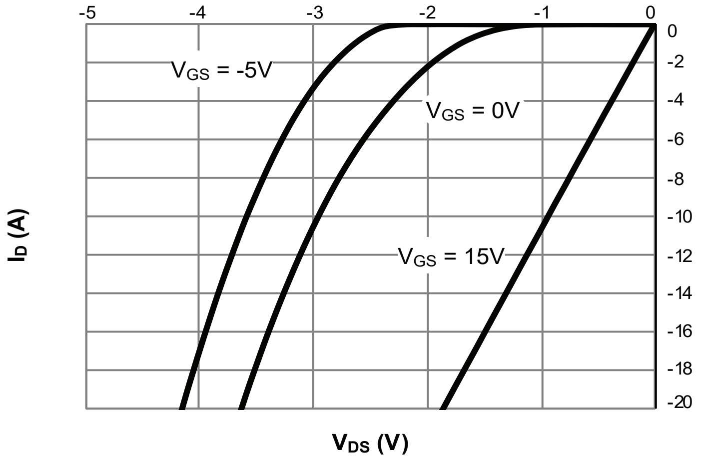


Figure 8. Body-Diode Characteristics at 175°C

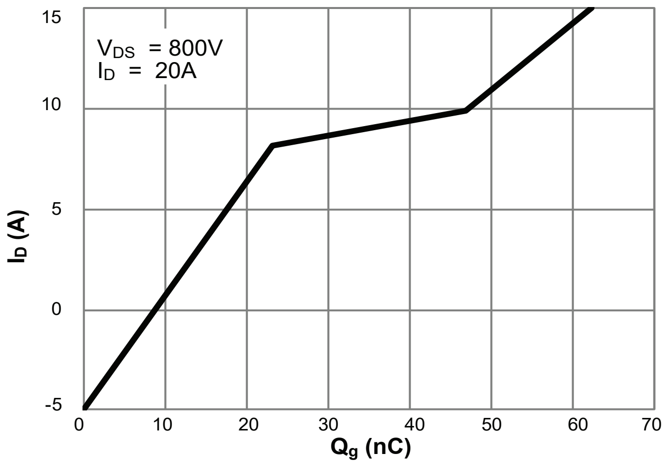


Figure 9. Gate-Charge Characteristics

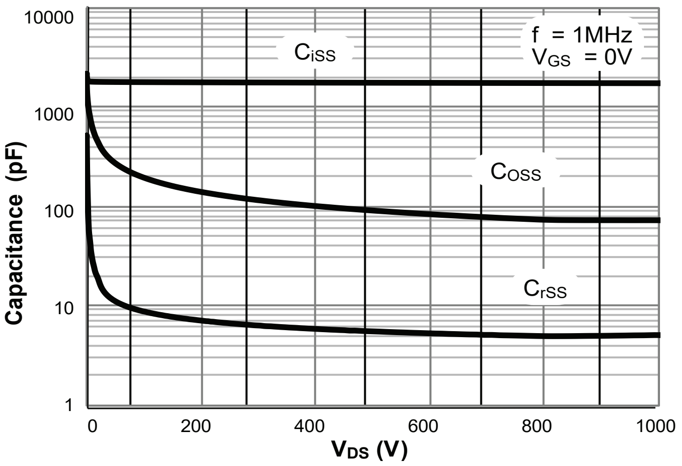


Figure 10. Capacitance Characteristics

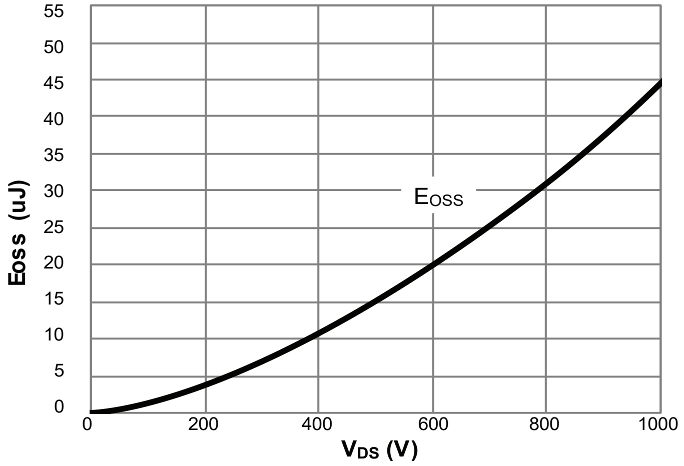


Figure 11. Coss stored Energy

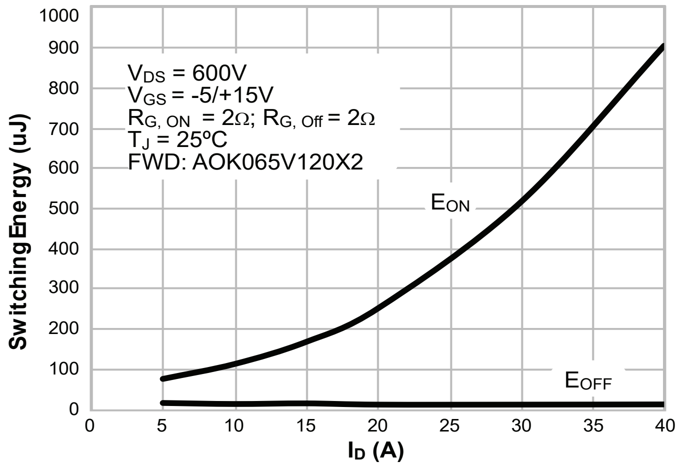


Figure 12. Switching Energy vs. Drain Current

Typical Electrical and Thermal Characteristics

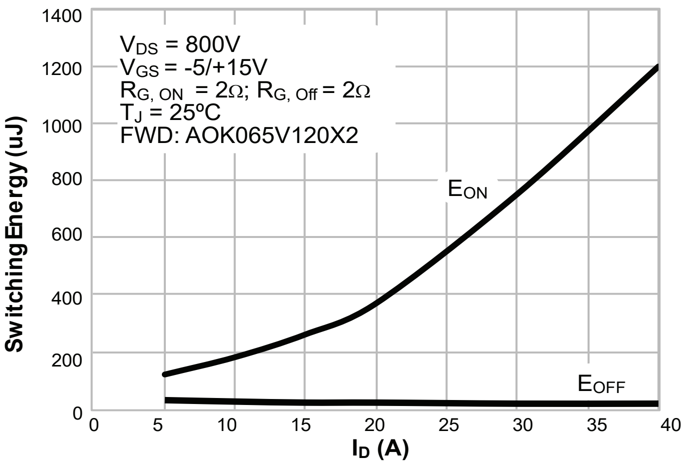


Figure 13. Switching Energy vs. Drain Durrent

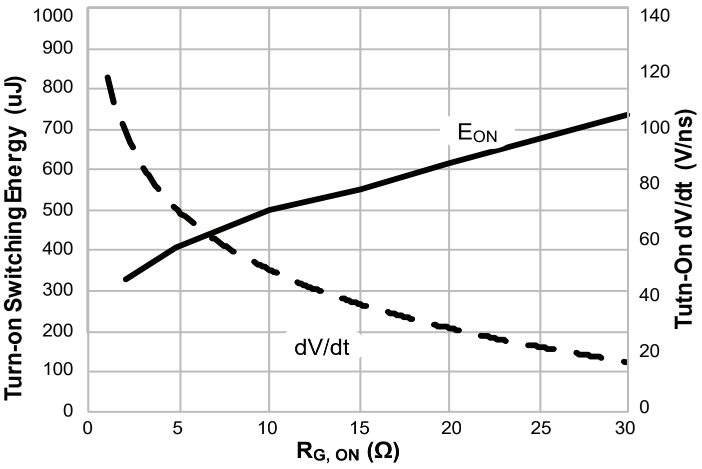


Figure 14. Turn-On Energy and dV/dt vs. External Gate Resistance

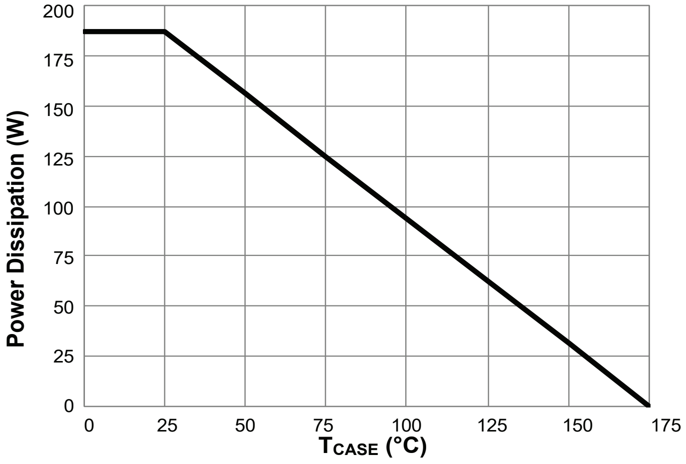


Figure 15. Power De-rating (Note I)

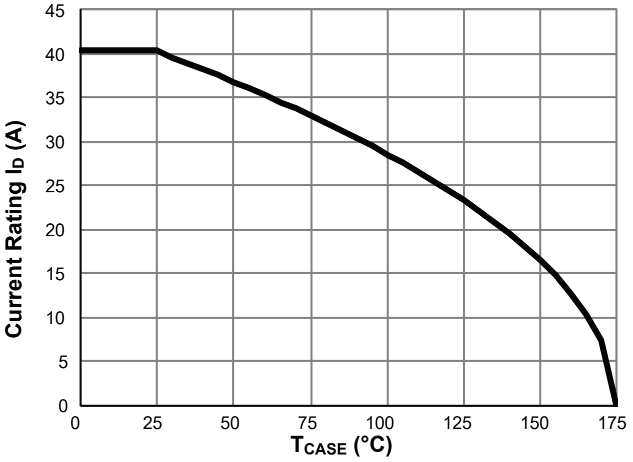


Figure 16. Current De-rating (Note I)

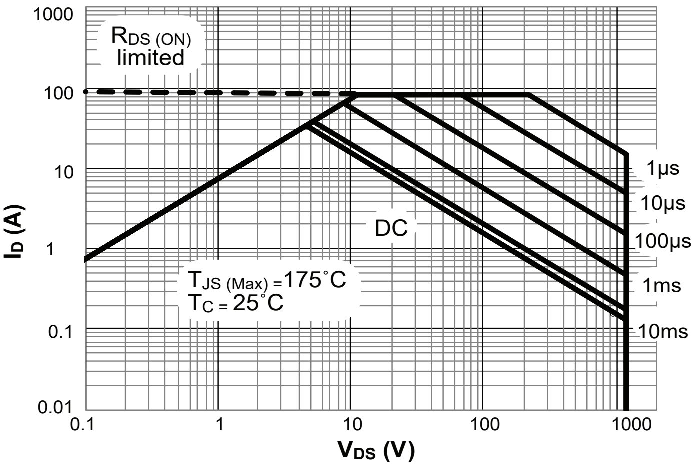


Figure 17. Maximum Forward Biased Safe Operating Area for AOK065V120X2 (Note I)

Typical Electrical and Thermal Characteristics

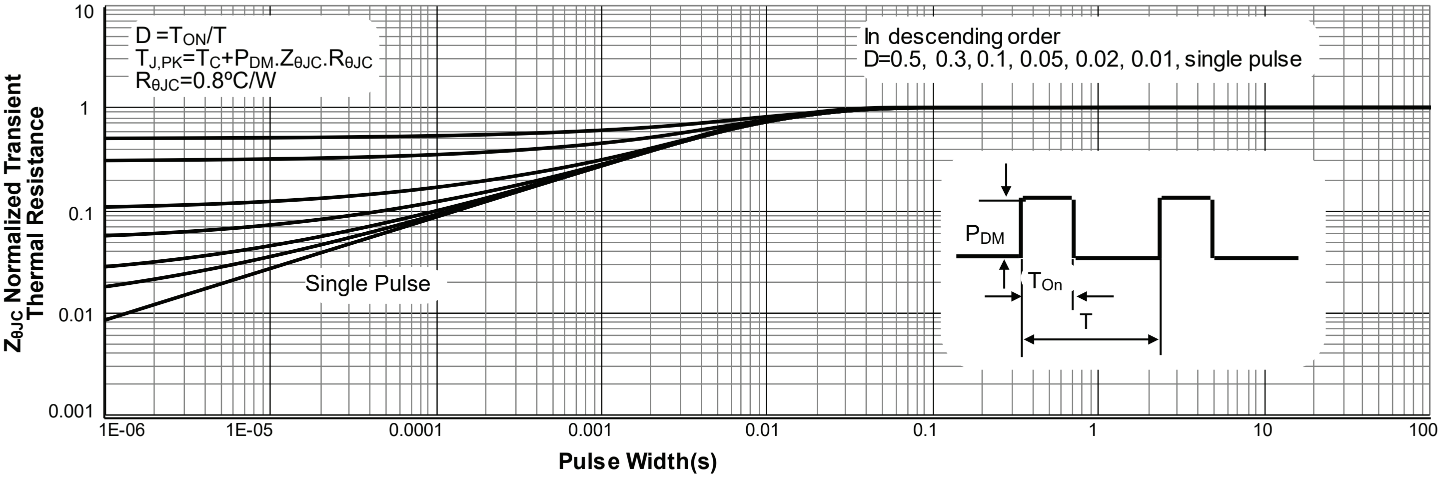
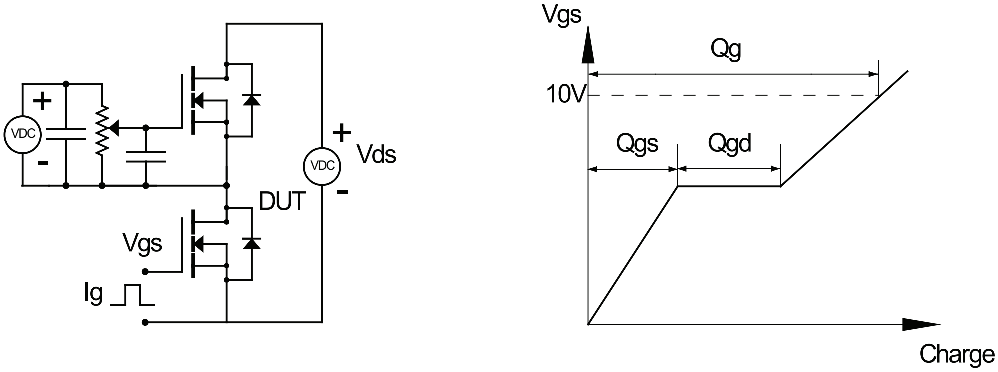


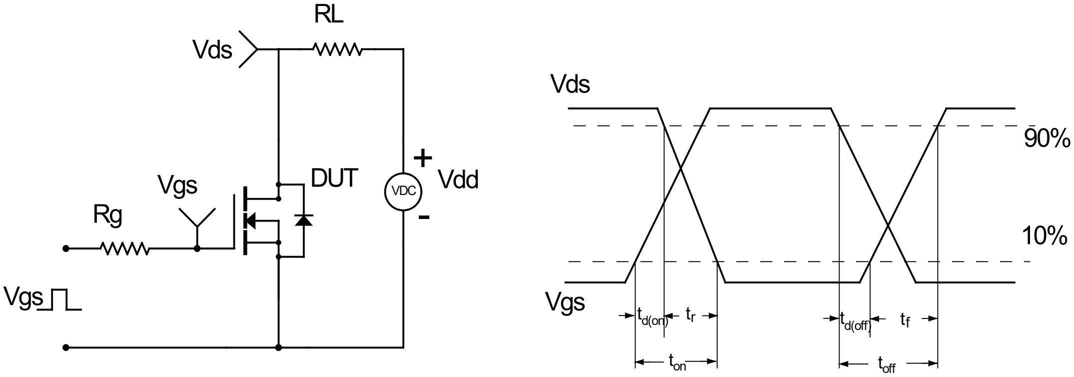
Figure 18. Normalized Maximum Transient Thermal Impedance for AOK065V120X2 (Note I)

Test Circuits and Waveforms

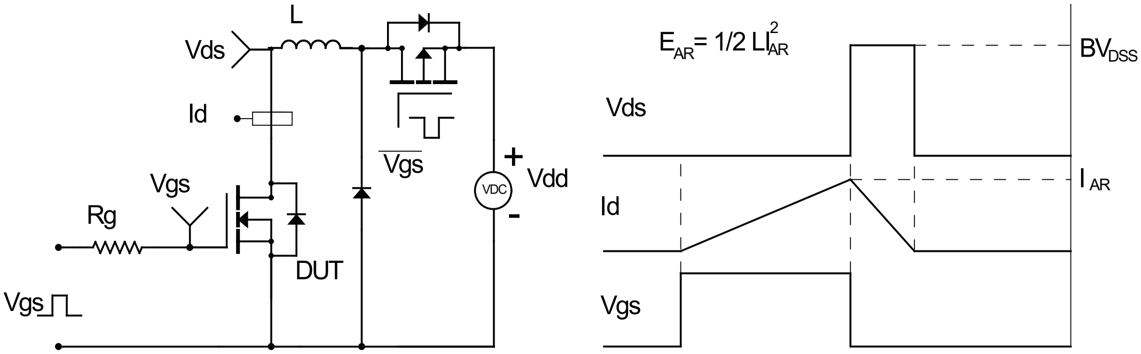
Gate Charge Test Circuits and Waveforms



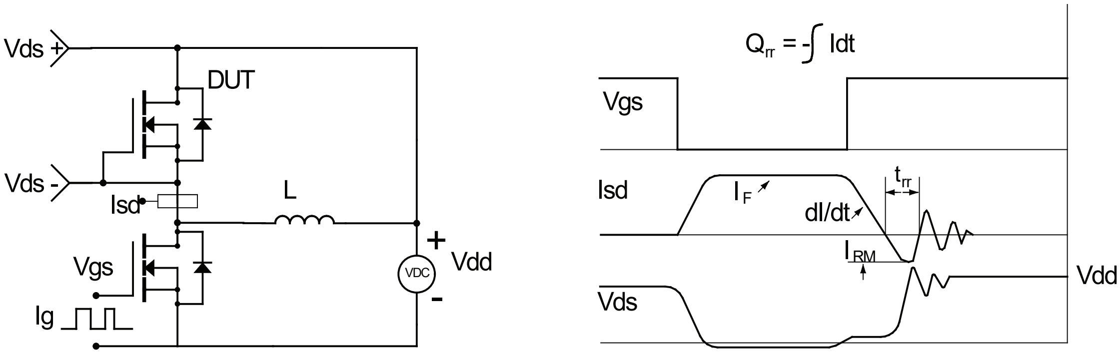
Resistive Switching Test Circuit and Waveforms



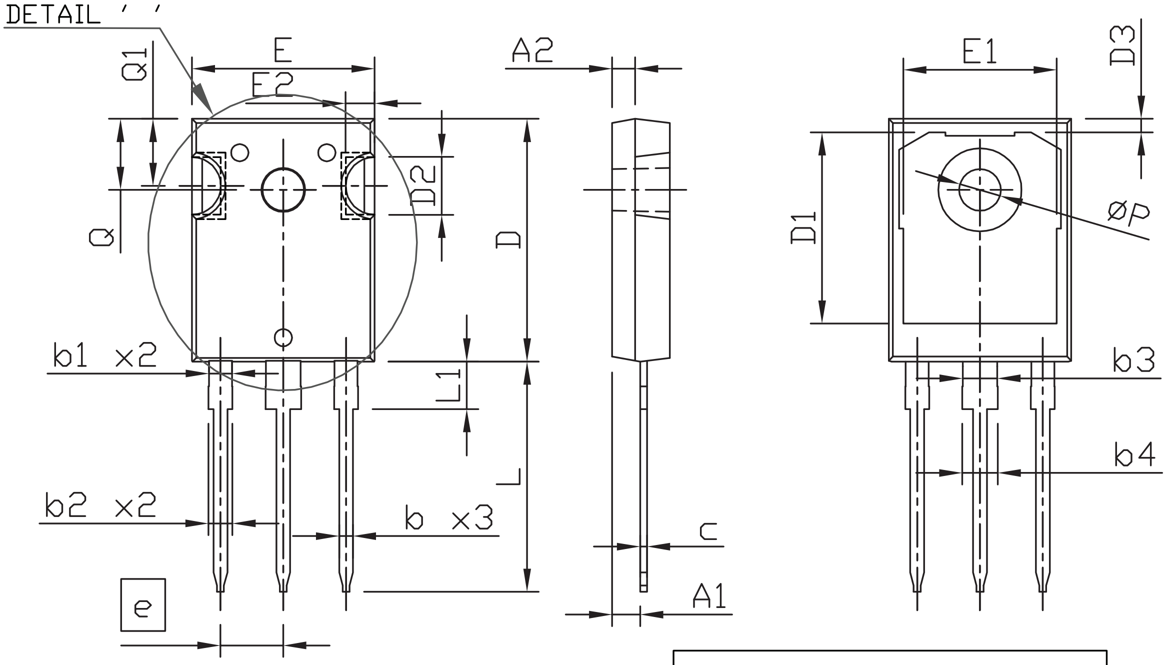
Unclamped Inductive Switching (UIS) Test Circuit and Waveforms

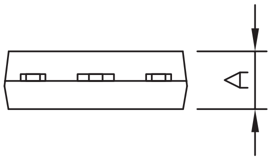


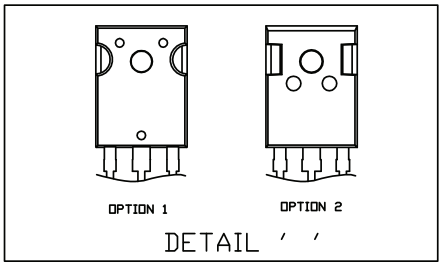
Gate Charge Test Circuits and Waveforms



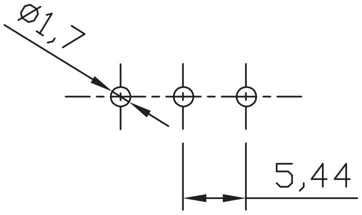
Package Dimensions, TO247-3L







RECOMMENDED LAND PATTERN



UNIT: mm

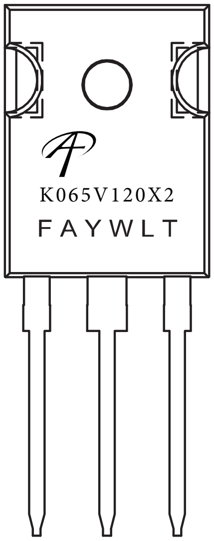
SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.90	5.00	5.10	0.193	0.197	0.201
A1	2.31	2.42	2.52	0.091	0.095	0.099
A2	1.90	2.00	2.10	0.075	0.079	0.083
b	1.16	1.22	1.27	0.046	0.048	0.050
b1	1.96	2.02	2.07	0.078	0.080	0.081
b2	2.00	2.10	2.20	0.079	0.083	0.087
b3	2.96	3.02	3.07	0.117	0.119	0.121
b4	3.00	3.10	3.20	0.118	0.122	0.126
c	0.59	0.62	0.66	0.023	0.024	0.026
D	20.90	21.00	21.10	0.823	0.827	0.831
D1	16.25	16.55	16.85	0.640	0.652	0.663
D2	5.00 TYP			0.197 TYP		
D3	1.05	1.20	1.35	0.041	0.047	0.053
e	5.44 BSC			0.214 BSC		
E	15.70	15.80	15.90	0.618	0.622	0.626
E1	13.06	13.26	13.50	0.514	0.522	0.530
E2	2.50 TYP			0.098 TYP		
L	19.72	19.92	20.12	0.776	0.784	0.792
L1	---	---	4.30	---	---	0.169
Q	6.15 BSC			0.242 BSC		
Q1	5.60	5.80	6.00	0.220	0.228	0.236
ØP	3.55	3.60	3.70	0.140	0.142	0.146

NOTE

1. PAKCAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
   MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
2. CONTROLLING DIMENSION IS MILLIMETER.
   CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

Part Marking

TO-247-3L



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2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.